In the Claims:

Claim 1 (currently amended): A method for reducing resist height erosion in a gate etch process, said method comprising steps of:

forming a first resist mask on an anti-reflective coating layer situated over a substrate, said first resist mask having a first width;

trimming said first resist mask to form a second resist mask, said second resist mask having a second width, said second width being less than said first width;

performing an HBr plasma treatment on said second resist mask;

wherein said HBr plasma treatment causes a vertical etch rate of said second resist mask to decrease; and wherein said HBr plasma treatment causes said vertical etch rate of said second resist mask to decrease by between approximately 40.0 percent and 80.0 percent.

Claim 2 (original): The method of claim 1 wherein said step of trimming said first resist mask to form a second resist mask comprises etching said anti-reflective coating layer.

Claim 3 (canceled)

Claim 4 (original): The method of claim 1 further comprising a step of etching said anti-reflective coating layer.

Claim 5 (original): The method of claim 1 wherein said anti-reflective coating layer comprises an organic material.

Claim 6 (original): The method of claim 1 further comprising a step of etching a hard mask layer.

Claim 7 (original): The method of claim 1 wherein said anti-reflective coating layer comprises an inorganic material.

Claims 8-13 (canceled)

Claim 14 (currently amended): A method for reducing resist height erosion in a gate etch process, said method comprising steps of:

forming a first resist mask on an anti-reflective coating layer situated over a substrate, said first resist mask having a first width;

performing an HBr plasma treatment on said first resist mask;

trimming said first resist mask to form a second resist mask, said second resist mask having a second width, said second width being less than said first width;

wherein said HBr plasma treatment causes a vertical etch rate of said first resist mask to decrease; wherein said HBr plasma treatment causes an increase in a lateral etch rate of said first resist mask.

Claim 15 (original): The method of claim 14 wherein said step of trimming said first resist mask to form a second resist mask comprises etching said anti-reflective coating layer.

Claim 16 (original): The method of claim 14 wherein said second width is between approximately 25.0 nanometers and approximately 50.0 nanometers.

Claim 17 (canceled)

Claim 18 (original): The method of claim 14 further comprising a step of etching said anti-reflective coating layer.

Claim 19 (original): The method of claim 14 wherein said anti-reflective coating layer comprises an organic material.

Claim 20 (original): The method of claim 14 wherein said anti-reflective coating layer comprises an inorganic material.